

SILICON PLANAR
SWITCHING TRANSISTORS

2N 2218, 2219, 2221, 2222

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CDIL Data Sheet

9/10 301-0545

2N2218 TO 2N2222 ARE NPN SILICON SMALL SIGNAL GENERAL PURPOSE AMPLIFIER AND SWITCH.

SWITCHING AND LINEAR APPLICATION. DC AND VHF AMPLIFIERS APPLICATIONS.

DESCRIPTION	SYMBOL	2218,19	2221,22	UNIT
Collector-Emitter Voltage	V _{CEO}	30	30	V
Collector-Base Voltage	V _{CBO}	60	60	V
Emitter-Base Voltage	V _{EB0}	5	5	V
Collector Current Continuous	I _C	800	800	mA
Power Dissipation At T _a =25 deg C	P _D	800	500	mW
Derate above 25 deg C		4.57	2.28	mW/deg C
Power Dissipation At T _c =25 deg C	P _D	3	1.2	mW
Derate above 25 deg C		17.1	6.85	mW/deg C
Storage Temperature	T _j , T _{stg}	-65 TO +200		°C

ELECTRICAL CHARACTERISTICS (T_a = 25 deg C unless otherwise specified)

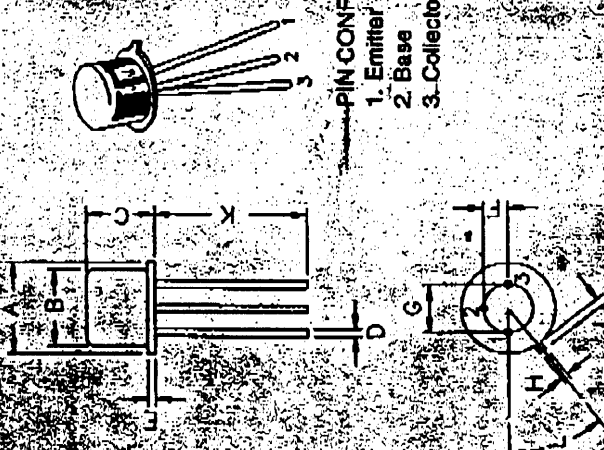
CHARACTERISTICS	SYMBOL	TEST CONDITION	VALUE		UNIT
			MIN	MAX	
Collector Emitter Breakdown Voltage	BV _{CEO}	I _C =10mA, I _B =0	30	-	V
Collector Base Breakdown Voltage	BV _{CBO}	I _C =10uA, I _E =0	60	-	V
Emitter Base Breakdown Voltage	BV _{EB0}	I _E =10uA, I _C =0	5	-	V
Collector Leakage Current	I _{CBO}	V _{CB} =50V, I _E =0	-	10	μA
		V _{CB} =50V, I _E =0 T _a =150deg C	-	10	μA
Collector-Emitter Saturation Voltage	V _{CE (sat)†}	I _C =150mA, I _B =15mA	-	0.4	V
		I _C =500mA, I _B =50mA	-	1.6	V
Base-Emitter Saturation Voltage	V _{BE (sat)†}	I _C =150mA, I _B =15mA	0.6	1.3	V
		I _C =500mA, I _B =50mA	-	2.6	V

Continental Device India Ltd.



TO-18

P2/2



PIN CONFIGURATION

- 1. Emitter
- 2. Base
- 3. Collector

DIM	MIN	MAX
A	5,24	5,84
B	4,52	4,97
C	4,31	5,33
D	0,40	0,53
E	-	0,76
F	-	1,27
G	-	2,97
H	0,91	1,17
J	0,71	1,21
K	12,7	-
L	45 DEG	-

ALL DIMENSIONS ARE IN M.M.